



PMDXB950UPE

20 V, dual P-channel Trench MOSFET

10 September 2013

Product data sheet

1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: $1.1 \times 1.0 \times 0.37$ mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance $R_{DS(on)} = 1.02 \Omega$

3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
V_{DS}	drain-source voltage	$T_J = 25^\circ\text{C}$		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = -4.5$ V; $T_{amb} = 25^\circ\text{C}$	[1]	-	-	-500	mA
Static characteristics (per transistor)							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5$ V; $I_D = -500$ mA; $T_J = 25^\circ\text{C}$		-	1.02	1.4	Ω

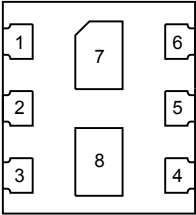
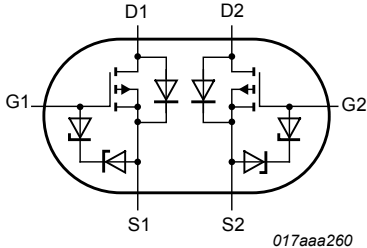
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



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5. Pinning information

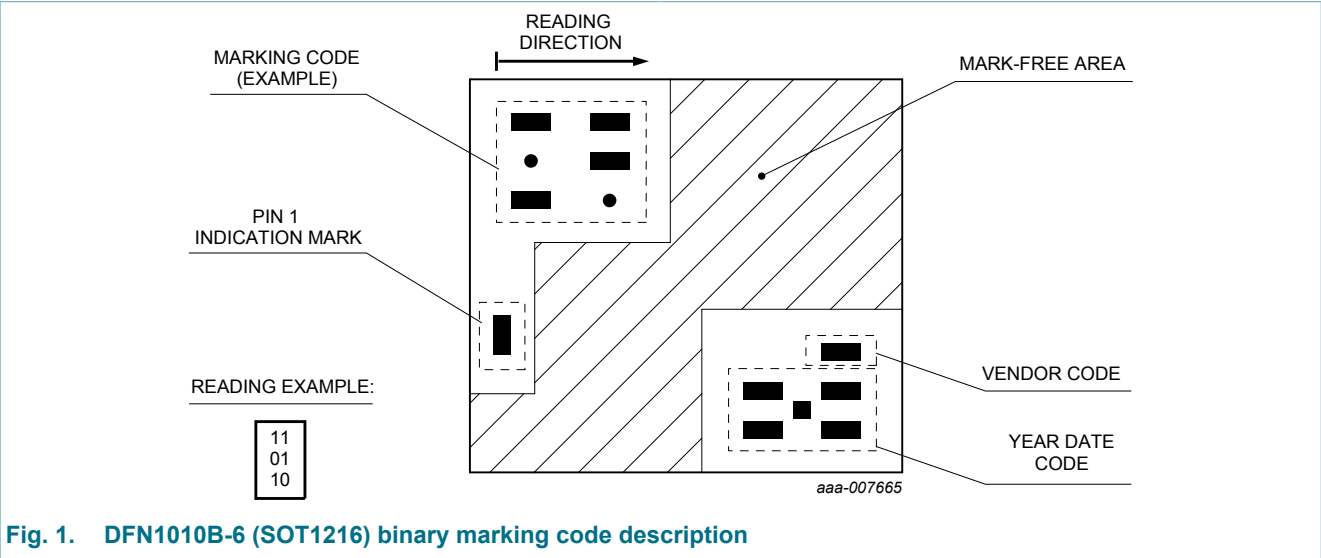
Table 2. Pinning information					
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	S1	source TR1	 <p>Transparent top view DFN1010B-6 (SOT1216)</p>	 <p>017aaa260</p>	
2	G1	gate TR1			
3	D2	drain TR2			
4	S2	source TR2			
5	G2	gate TR2			
6	D1	drain TR1			
7	D1	drain TR1			
8	D2	drain TR2			

6. Ordering information

Table 3. Ordering information			
Type number	Package		
	Name	Description	Version
PMDXB950UPE	DFN1010B-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMDXB950UPE	10 10 00



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-500	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-300	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-2	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	380	mW
		T _{sp} = 25 °C		-	4025	mW
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	-350	mA
Per device						
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

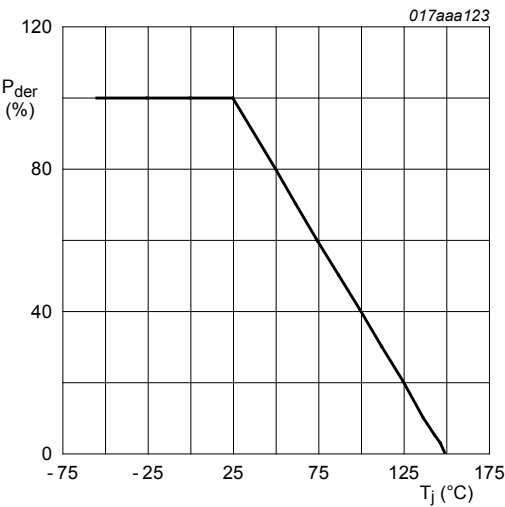


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

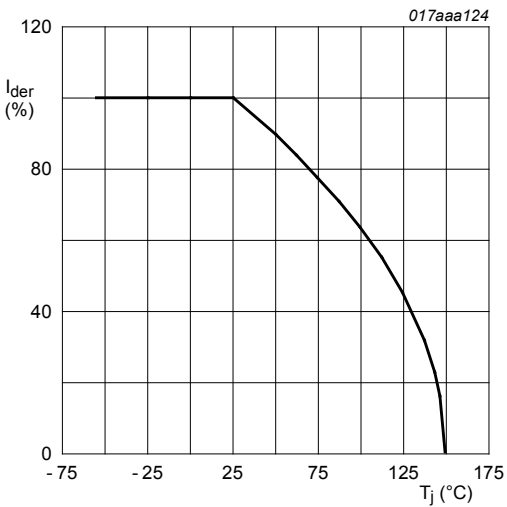


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

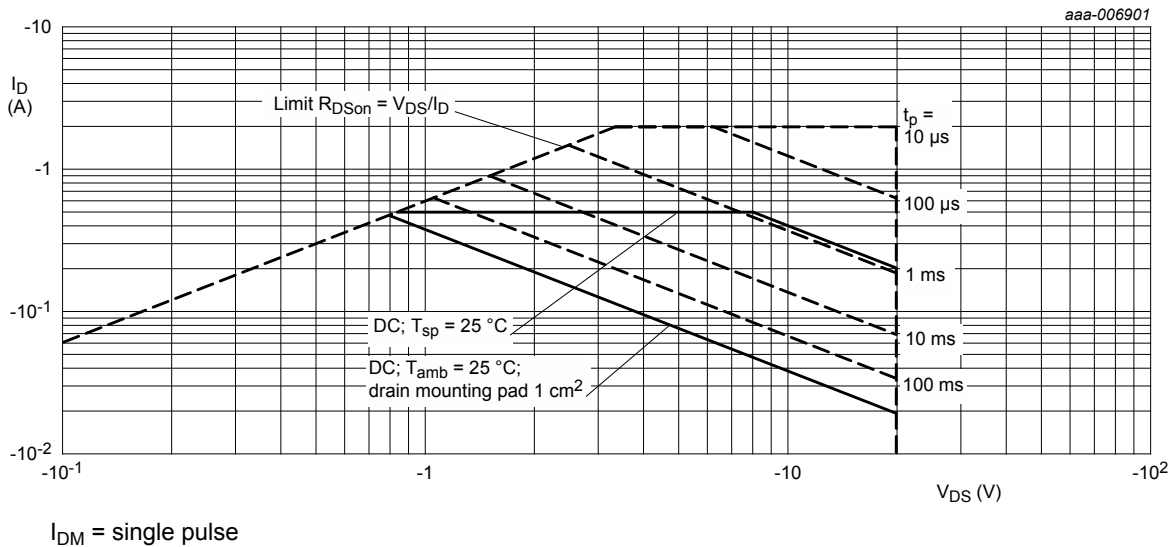


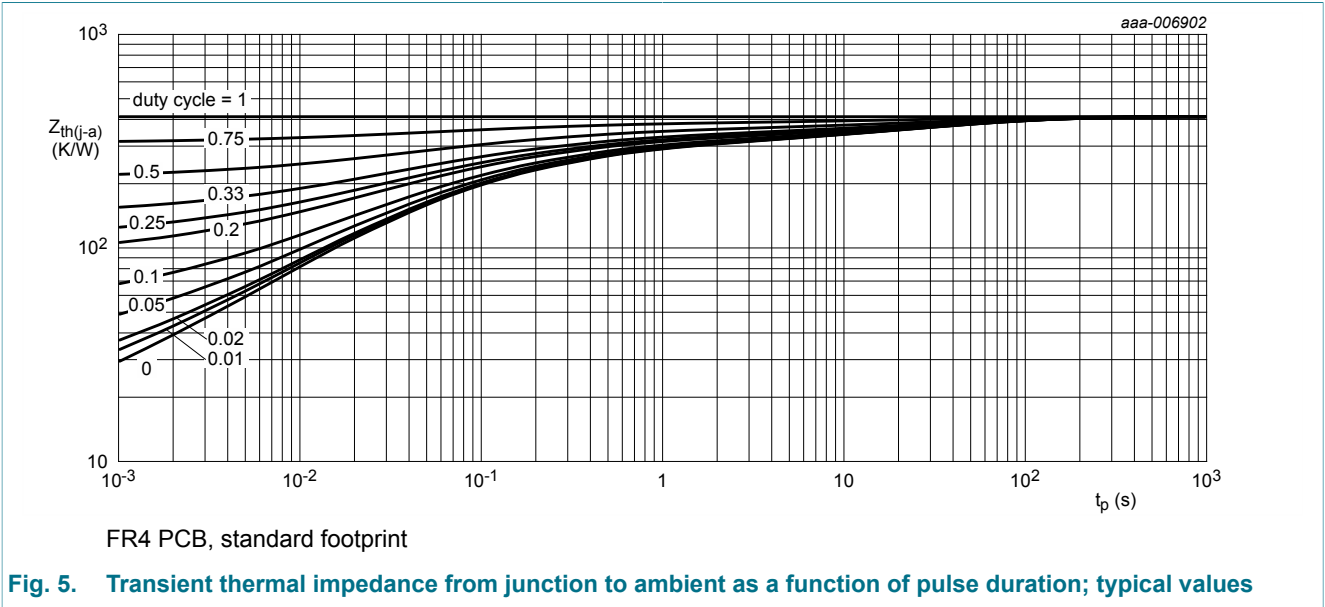
Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	410	475	K/W
			[2]	-	285	330	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	27	31	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



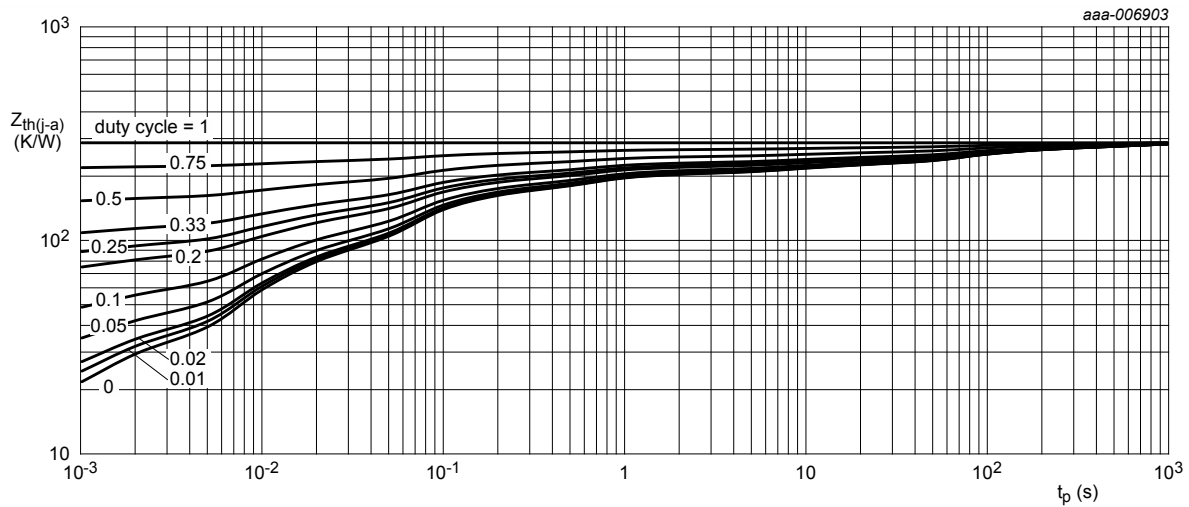


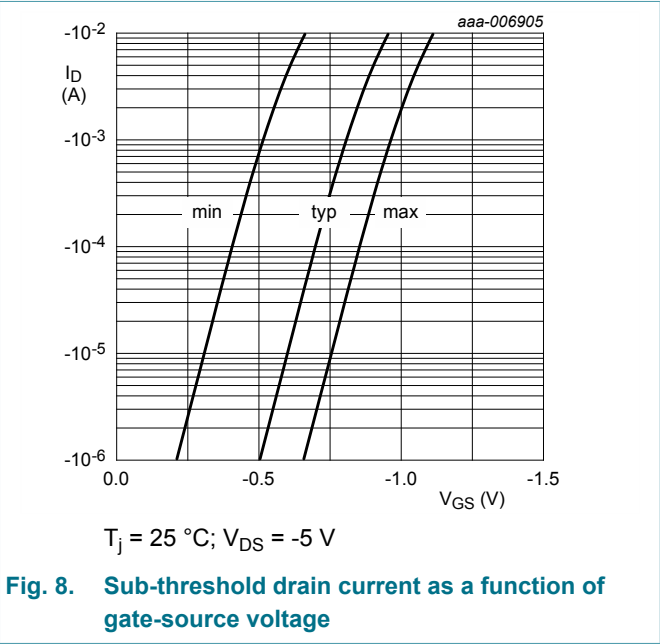
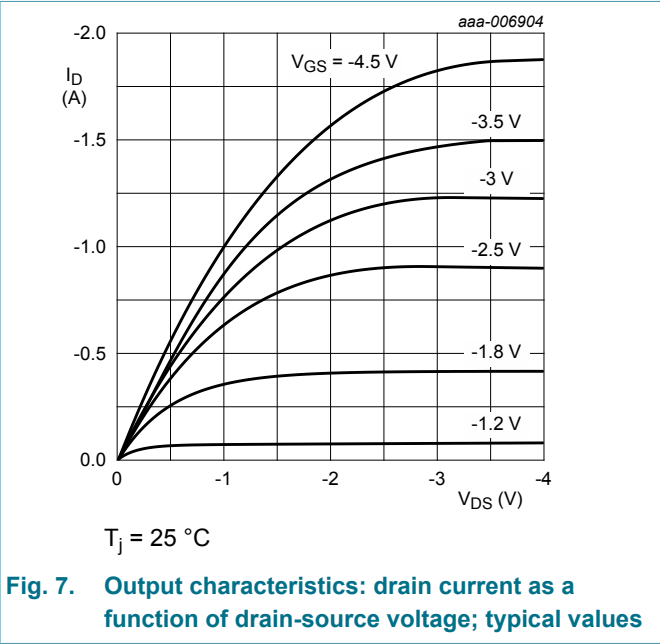
Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics (per transistor)						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A$; $V_{GS} = 0 V$; $T_j = 25^\circ C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25^\circ C$	-0.45	-0.7	-0.95	V
I_{DSS}	drain leakage current	$V_{DS} = -20 V$; $V_{GS} = 0 V$; $T_j = 25^\circ C$	-	-	-1	μA
		$V_{DS} = -20 V$; $V_{GS} = 0 V$; $T_j = 150^\circ C$	-	-	-10	μA
I_{GSS}	gate leakage current	$V_{GS} = 8 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$	-	-	10	μA
		$V_{GS} = -8 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$	-	-	-10	μA
		$V_{GS} = 4.5 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$	-	-	1	μA
		$V_{GS} = -4.5 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$	-	-	-1	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 V$; $I_D = -500 mA$; $T_j = 25^\circ C$	-	1.02	1.4	Ω
		$V_{GS} = -4.5 V$; $I_D = -500 mA$; $T_j = 150^\circ C$	-	1.54	2.1	Ω
		$V_{GS} = -2.5 V$; $I_D = -200 mA$; $T_j = 25^\circ C$	-	1.27	2.2	Ω
		$V_{GS} = -1.8 V$; $I_D = -40 mA$; $T_j = 25^\circ C$	-	1.7	3.3	Ω
		$V_{GS} = -1.5 V$; $I_D = -10 mA$; $T_j = 25^\circ C$	-	2.3	5	Ω
		$V_{GS} = -1.2 V$; $I_D = -1 mA$; $T_j = 25^\circ C$	-	3.5	-	Ω
g_{fs}	forward transconductance	$V_{DS} = -10 V$; $I_D = -500 mA$; $T_j = 25^\circ C$	-	480	-	mS

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics (per transistor)							
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -450 mA; V _{GS} = -4.5 V; T _j = 25 °C		-	1.19	2.1	nC
Q _{GS}	gate-source charge			-	0.17	-	nC
Q _{GD}	gate-drain charge			-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	43	-	pF
C _{oss}	output capacitance			-	14	-	pF
C _{rss}	reverse transfer capacitance			-	8	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -10 V; I _D = -0.45 A; R _L = 22 Ω; V _{GS} = -4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	2.3	-	ns
t _r	rise time			-	5	-	ns
t _{d(off)}	turn-off delay time			-	13.5	-	ns
t _f	fall time			-	6	-	ns
Source-drain diode (per transistor)							
V _{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _j = 25 °C		-	-0.7	-1.2	V



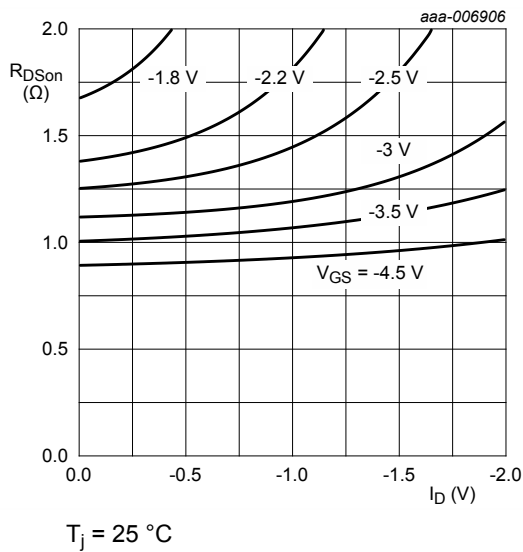


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

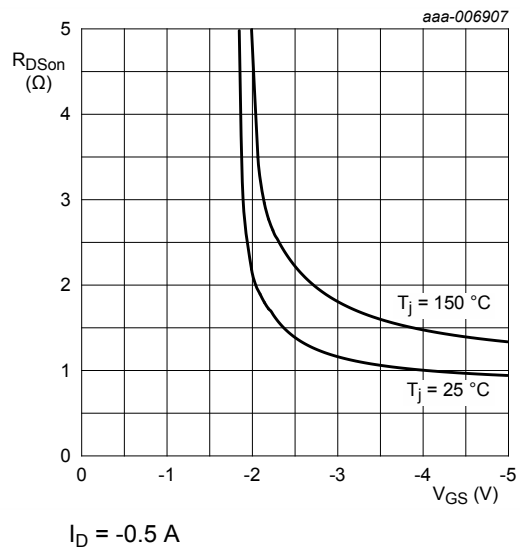


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

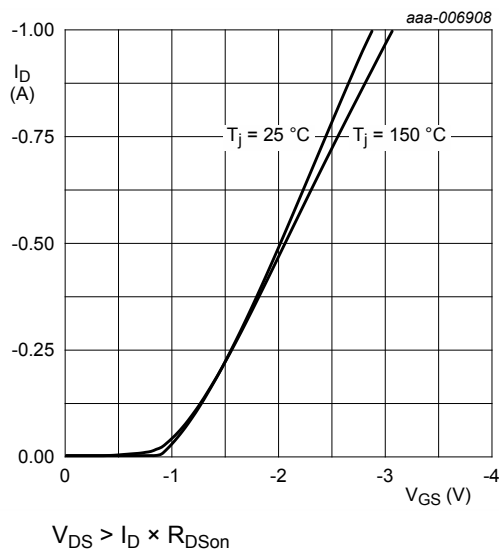


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

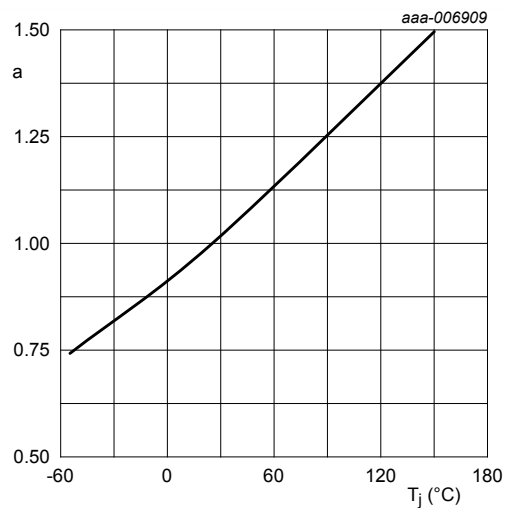


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

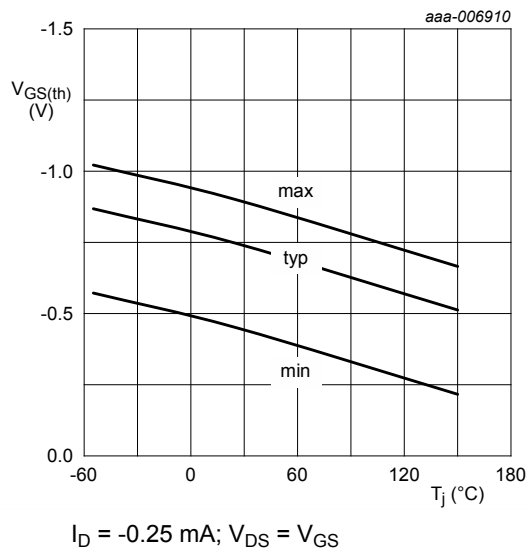


Fig. 13. Gate-source threshold voltage as a function of junction temperature

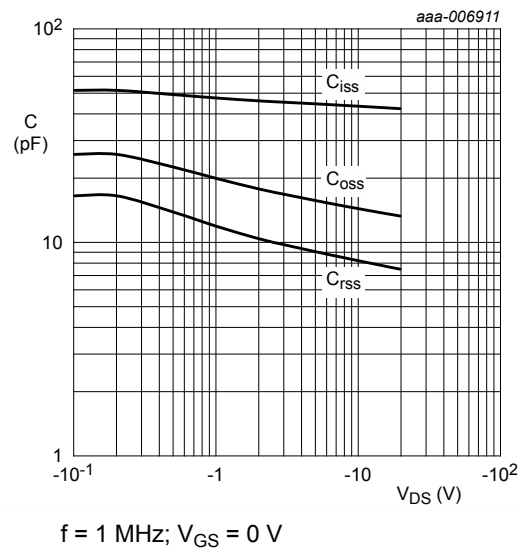


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

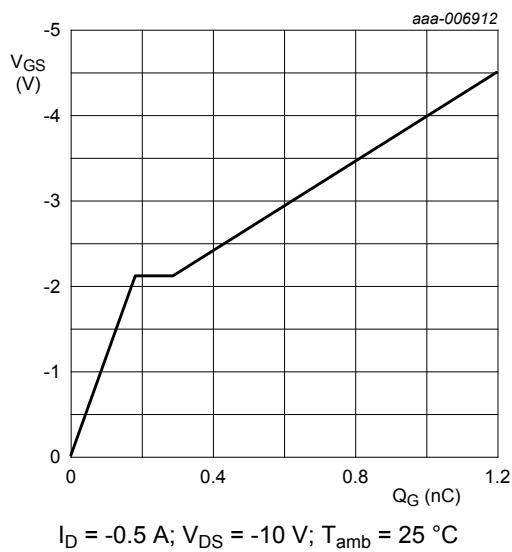


Fig. 15. Gate-source voltage as a function of gate charge; typical values

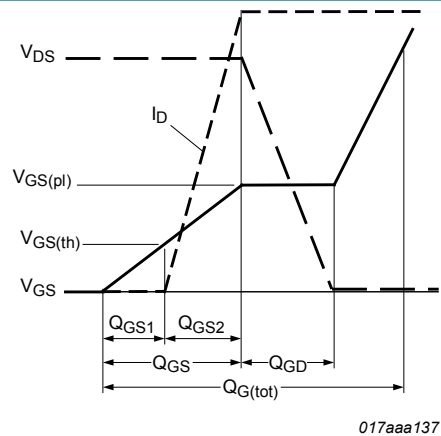
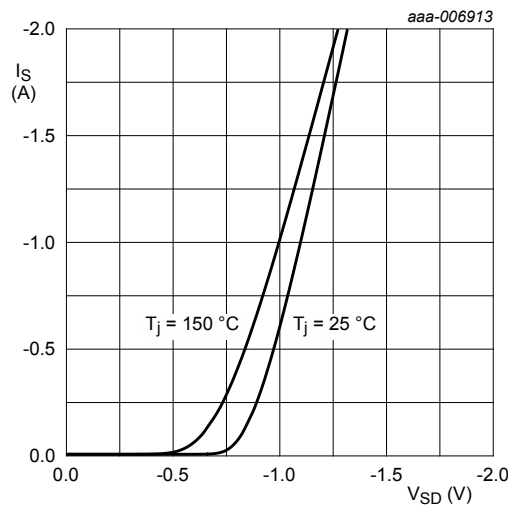


Fig. 16. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

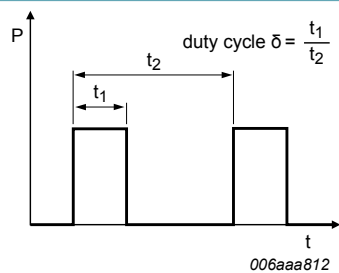


Fig. 18. Duty cycle definition

12. Package outline

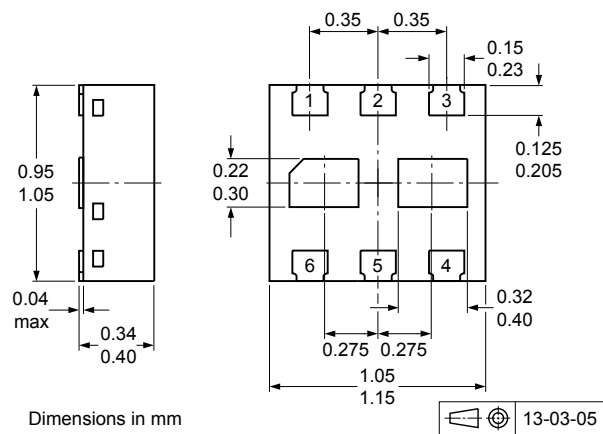


Fig. 19. Package outline DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDXB950UPE v.1	20130910	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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